

2N2219AHR

Hi-Rel NPN bipolar transistor 40 V, 0.8 A

Datasheet — production data

Features

BV _{CEO}	40 V
I _C (max)	0.8 A
H _{FE} at 10 V - 150 m	> 100
Operating temperature range	- 65 °C to + 200 °C

- Hi-Rel NPN bipolar transistor
- Linear gain characteristics
- ESCC qualified
- European preferred part list EPPL
- Radiation level: lot specific total dose contact marketing for specified level

Description

The 2N2219AHR is a silicon planar epitaxial NPN transistor in a TO-39 package. It is specifically designed for aerospace Hi-Rel applications, and ESCC qualified in accordance with the 5201-003 specification. In case of discrepancies between this datasheet and ESCC detailed specification, the latter prevails.

TO-39	

Figure 1. Internal schematic diagram

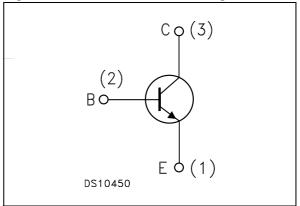


Table 1.	Device summary
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Order codes	Package	Lead finish	Marking	Туре	EPPL	Packaging
2N2219AHR	TO-39	Gold Solder Dip	520100301 520100302	ESCC Flight	Yes	Strip pack
2N2219AT1	TO-39	Gold	2N2219AT1	Engineering model		Strip pack

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This is information on a product in full production.

1 Electrical ratings

Table 2.	Absolute maximum ratings
	Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	75	V
V _{CEO}	Collector-emitter voltage ($I_B = 0$)	40	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	6	V
Ι _C	Collector current	0.8	Α
P _{TOT}	Total dissipation at $T_{amb} \le 25^{\circ}C$ Total dissipation at $T_{c} \le 25^{\circ}C$	0.8 3	W W
T _{STG}	Storage temperature	-65 to 200	°C
Τ _J	Max. operating junction temperature	200	°C

Table 3. Thermal data

Symbol	Parameter		Value	Unit
R _{thJC}	Thermal resistance junction-case	max	58	°C/W
R _{thJA}	Thermal resistance junction-ambient	max	218	°C/W

2 Electrical characteristics

 T_{case} = 25 °C unless otherwise specified.

Table 4.	Electrical characteristics					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 60 V V _{CB} = 60 V, T _{amb} = 150 °C		-	10 10	nA μA
I _{EBO}	Emitter cut-off current $(I_{C} = 0)$	V _{EB} = 3 V		-	10	nA
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 10 μA	75	-		v
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage $(I_B = 0)$	I _C = 10 mA	40	-		v
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 10 μA	6	-		v
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_{C} = 150$ mA, $I_{B} = 15$ mA $I_{C} = 500$ mA, $I_{B} = 50$ mA		-	0.3 1	V V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C = 150 mA, I _B = 15 mA		-	1.2	V
h _{FE} ⁽¹⁾	DC current gain	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $T_{amb} = -55 \text{ °C}$	75 100 40 35	-	300	
h _{fe}	Small signal current gain	$V_{CE} = 20 \text{ V}, I_{C} = 20 \text{ mA}$ f = 100 MHz	2.5	-		
C _{CBO}	Output capacitance (I _E = 0)	V _{CB} = 10 V 100 kHz ≤ f ≤1 MHz		-	8	pF
t _{on}	Turn-on time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$ $I_{B1} = 15 \text{ mA}$		-	35	ns
t _{off}	Turn-off time	$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}$ $I_{B1} = -I_{B2} = 15 \text{ mA}$		-	300	ns

 Table 4.
 Electrical characteristics

1. Pulsed duration = 300 μ s, duty cycle $\leq 2\%$



2.1 Electrical characteristics (curves)

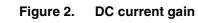


Figure 3.

e 3. Collector emitter saturation voltage

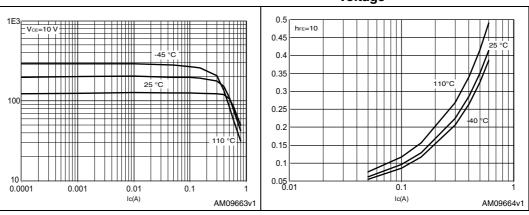
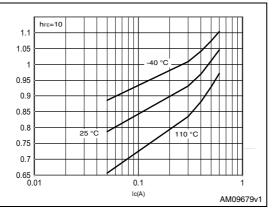


Figure 4. Base emitter saturation voltage





2.2 Test circuit

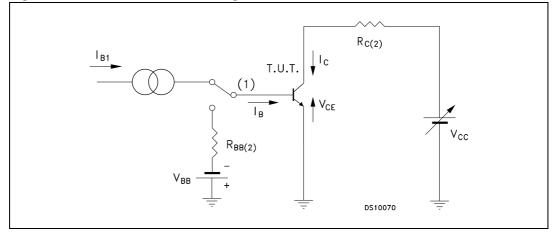


Figure 5. Resistive load switching test circuit

- 1. Fast electronic switch
- 2. Non-inductive resistor



3 Package mechanical data

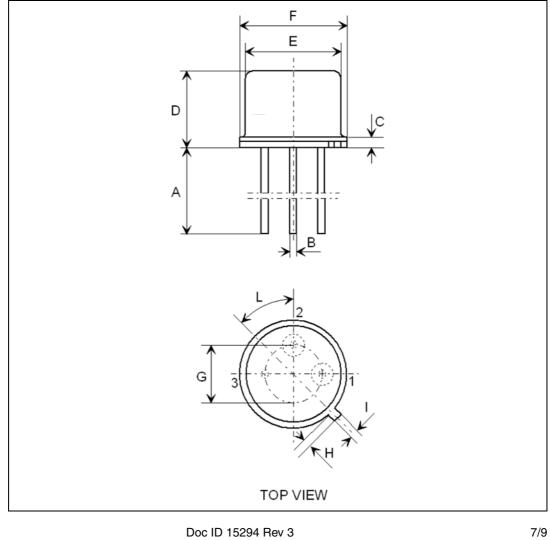
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Table 5.	TO-39 mechanical data
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Dim.		mm	
	Min.	Тур.	Max.
A		12.70	14.20
В		0.40	0.49
С		0.58	0.74
D		6.00	6.40
E	_	8.15	8.25
F	-	9.10	9.20
G		4.93	5.23
Н		0.85	0.95
I		0.75	0.85
L		42°	48°





4 Revision history

Table 6.Document revision history

Date	Revision	Changes
09-Jan-2009	1	Initial release
05-Jan-2010	2	Modified Table 1 on page 1
04-Oct-2012	3	Minor text changes. Section 2.1: Electrical characteristics (curves) has been added.



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